



2SC536M (3DG536M)

2SC536KM (3DG536KM)

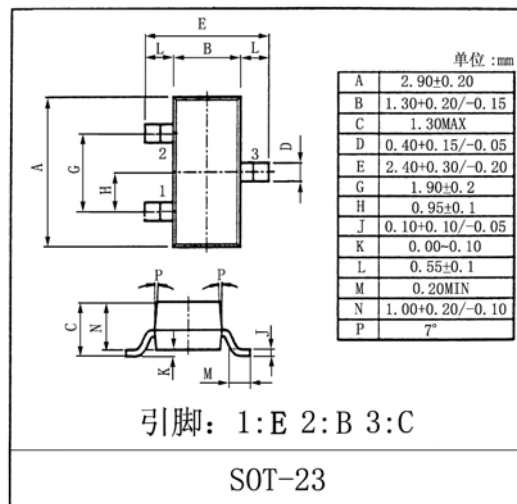
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途:用于小信号一般放大电路。

Purpose: Small signal general purpose amplifier applications.

极限参数/Absolute Maximum Ratings (Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit	
V _{CBO}	3DG536M 3DG536KM	40 55	V
V _{CEO}	3DG536M 3DG536KM	30 50	V
V _{EBO}		5.0	V
I _C		100	mA
I _{CP}		300	mA
P _C		250	mW
T _j		150	°C
T _{stg}		-55~150	°C



电性能参数/Electrical Characteristics (Ta=25°C)

参数符号 Symbol	测试条件 Test Condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
I _{CBO}	V _{CB} =35V I _E =0			1.0	μA
I _{EBO}	V _{EB} =4.0V I _C =0			1.0	μA
h _{FE}	V _{CE} =6.0V I _C =1.0mA	60		960	
V _{CE(sat)}	I _C =50mA I _B =5.0mA			0.5	V
f _T	V _{CE} =6.0V I _C =1.0mA		100		MHz
C _{ob}	V _{CB} =6.0V I _E =0 f=1.0MHz		3.5		pF
C _{c, rbb'}	V _{CB} =6.0V I _c =1.0mA f=31.9MHz		250		pS

h_{FE} 分档、印章/h_{FE} classifications、Marking:

h _{FE} 分档 h _{FE} Classifications	D	E	F	G	H
h _{FE} 范围 h _{FE} Range	60~120	100~200	160~320	280~560	480~960
印章 Marking	H53D	H53E	H53F	H53G	H53H



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